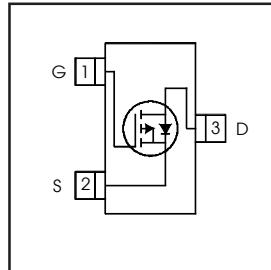


- Ultra Low On-Resistance
- P-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- 1.8V Gate Rated
- Lead-Free
- RoHS Compliant, Halogen-Free

### HEXFET® Power MOSFET



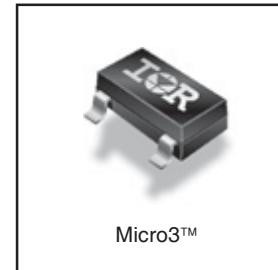
$V_{DSS} = -12V$

$R_{DS(on)} = 0.05\Omega$

### Description

These P-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



Micro3™

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLML6401TRPbF	Micro3™ (SOT-23)	Tape and Reel	3000	IRLML6401TRPbF

### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	-12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-4.3	
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-3.4	A
$I_{DM}$	Pulsed Drain Current ①	-34	
$P_D @ T_A = 25^\circ C$	Power Dissipation	1.3	
$P_D @ T_A = 70^\circ C$	Power Dissipation	0.8	W
	Linear Derating Factor	0.01	W/ $^\circ C$
$E_{AS}$	Single Pulse Avalanche Energy ②	33	mJ
$V_{GS}$	Gate-to-Source Voltage	$\pm 8.0$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ③	75	100	$^\circ C/W$

### Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

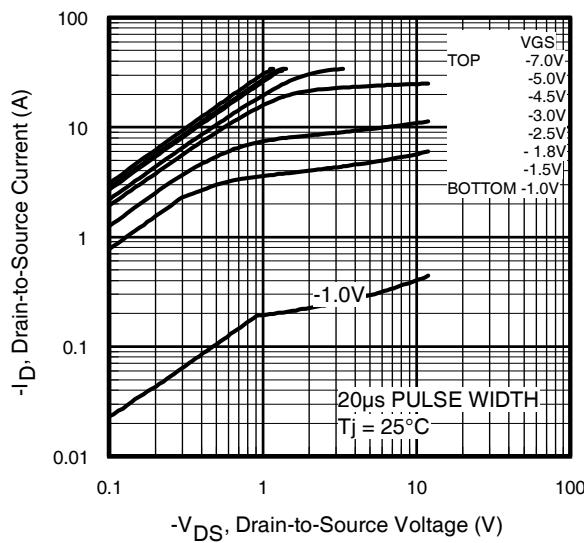
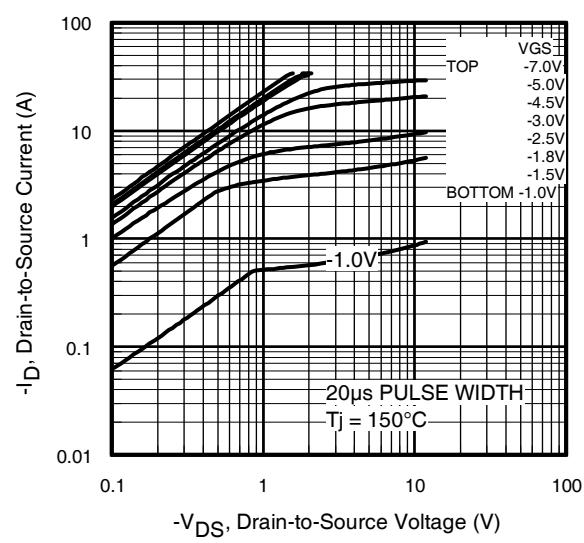
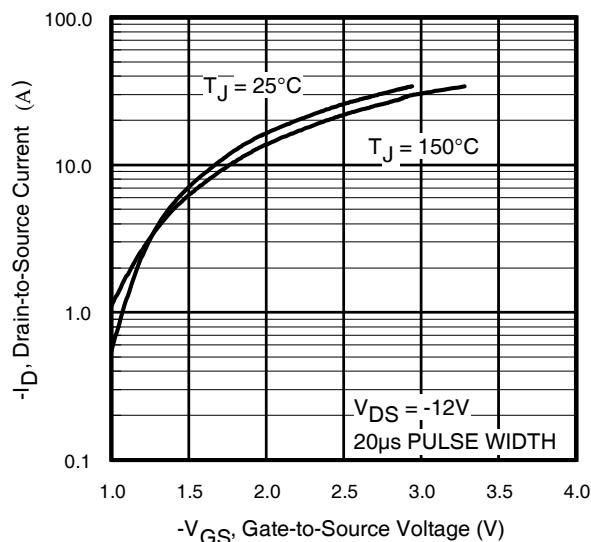
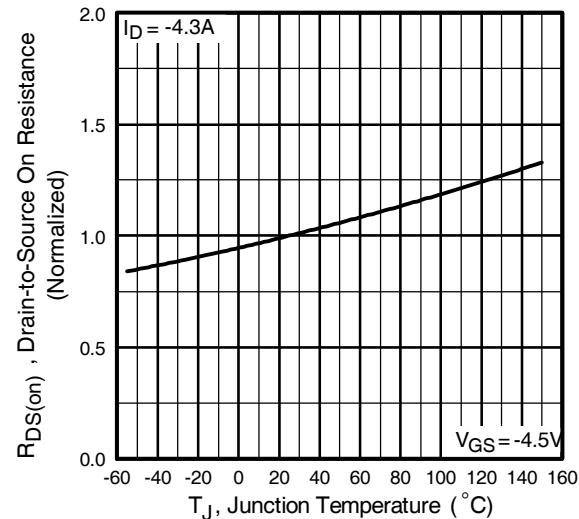
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	-12	—	—	V	$V_{GS} = 0\text{V}$ , $I_D = -250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}/\Delta T_J}$	Breakdown Voltage Temp. Coefficient	—	-0.007	—	$\text{V}/^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = -1\text{mA}$
$R_{DS(\text{on})}$	Static Drain-to-Source On-Resistance	—	—	0.050	$\Omega$	$V_{GS} = -4.5\text{V}$ , $I_D = -4.3\text{A}$ ②
		—	—	0.085		$V_{GS} = -2.5\text{V}$ , $I_D = -2.5\text{A}$ ②
		—	—	0.125		$V_{GS} = -1.8\text{V}$ , $I_D = -2.0\text{A}$ ②
$V_{GS(\text{th})}$	Gate Threshold Voltage	-0.40	-0.55	-0.95	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu\text{A}$
$g_f$	Forward Transconductance	8.6	—	—	S	$V_{DS} = -10\text{V}$ , $I_D = -4.3\text{A}$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-1.0	$\mu\text{A}$	$V_{DS} = -12\text{V}$ , $V_{GS} = 0\text{V}$
		—	—	-25		$V_{DS} = -9.6\text{V}$ , $V_{GS} = 0\text{V}$ , $T_J = 55^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	-100	$\text{nA}$	$V_{GS} = -8.0\text{V}$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 8.0\text{V}$
$Q_g$	Total Gate Charge	—	10	15	$\text{nC}$	$I_D = -4.3\text{A}$
$Q_{gs}$	Gate-to-Source Charge	—	1.4	2.1		$V_{DS} = -10\text{V}$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	2.6	3.9		$V_{GS} = -5.0\text{V}$ ②
$t_{d(on)}$	Turn-On Delay Time	—	11	—	$\text{ns}$	$V_{DD} = -6.0\text{V}$
$t_r$	Rise Time	—	32	—		$I_D = -1.0\text{A}$
$t_{d(off)}$	Turn-Off Delay Time	—	250	—		$R_D = 6.0\Omega$
$t_f$	Fall Time	—	210	—		$R_G = 89\Omega$ ②
$C_{iss}$	Input Capacitance	—	830	—	$\text{pF}$	$V_{GS} = 0\text{V}$
$C_{oss}$	Output Capacitance	—	180	—		$V_{DS} = -10\text{V}$
$C_{rss}$	Reverse Transfer Capacitance	—	125	—		$f = 1.0\text{MHz}$

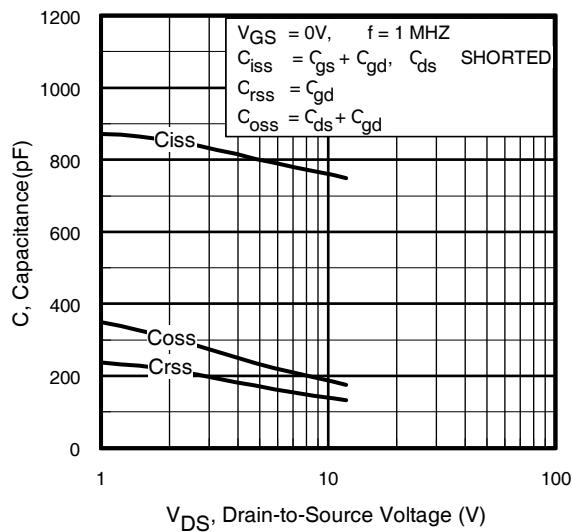
### Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-34		
$V_{SD}$	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}$ , $I_S = -1.3\text{A}$ , $V_{GS} = 0\text{V}$ ②
$t_{rr}$	Reverse Recovery Time	—	22	33	ns	$T_J = 25^\circ\text{C}$ , $I_F = -1.3\text{A}$
$Q_{rr}$	Reverse Recovery Charge	—	8.0	12	nC	$dI/dt = -100\text{A}/\mu\text{s}$ ②

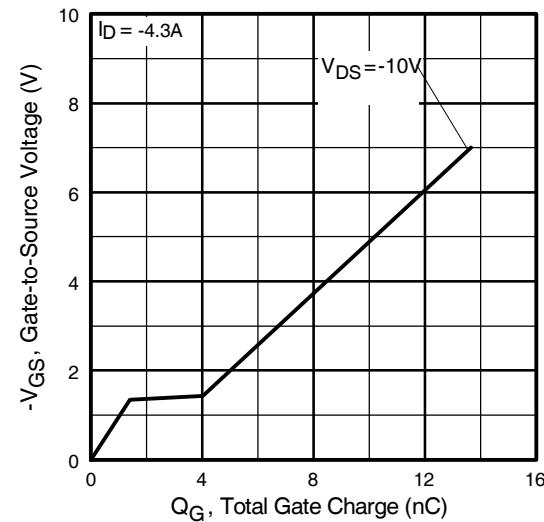
#### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ③ Surface mounted on 1" square single layer 1oz. copper FR4 board, steady state.
- ④ Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.5\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = -4.3\text{A}$ .

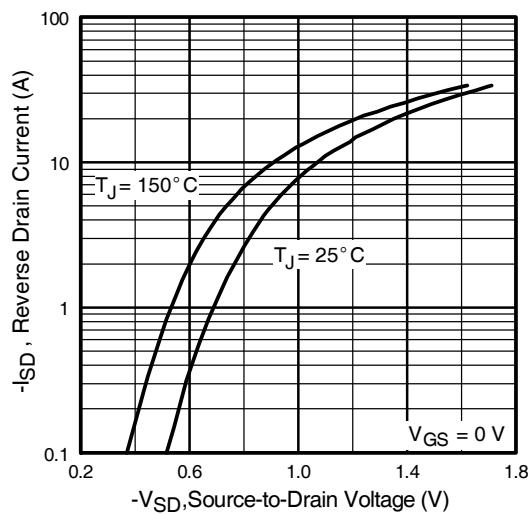
**Fig 1.** Typical Output Characteristics**Fig 2.** Typical Output Characteristics**Fig 3.** Typical Transfer Characteristics**Fig 4.** Normalized On-Resistance Vs. Temperature



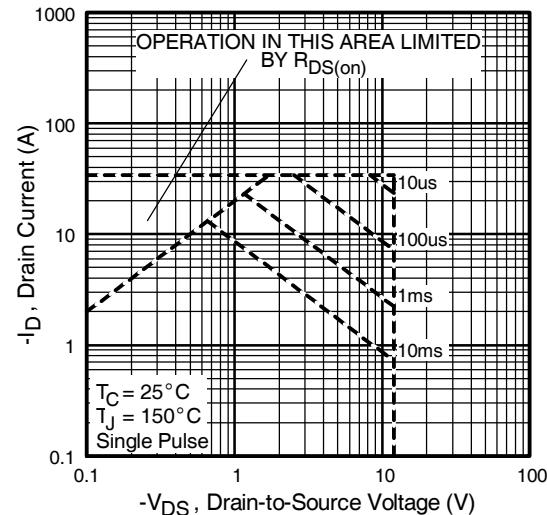
**Fig 5.** Typical Capacitance Vs.  
Drain-to-Source Voltage



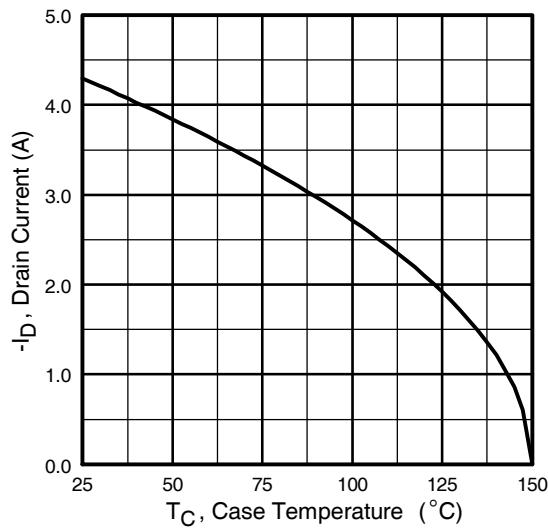
**Fig 6.** Typical Gate Charge Vs.  
Gate-to-Source Voltage



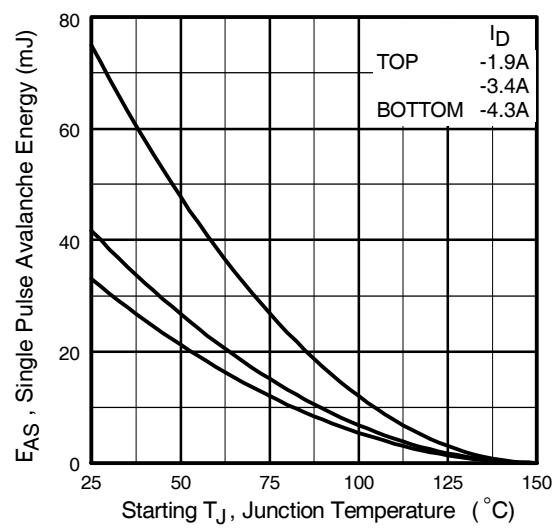
**Fig 7.** Typical Source-Drain Diode  
Forward Voltage



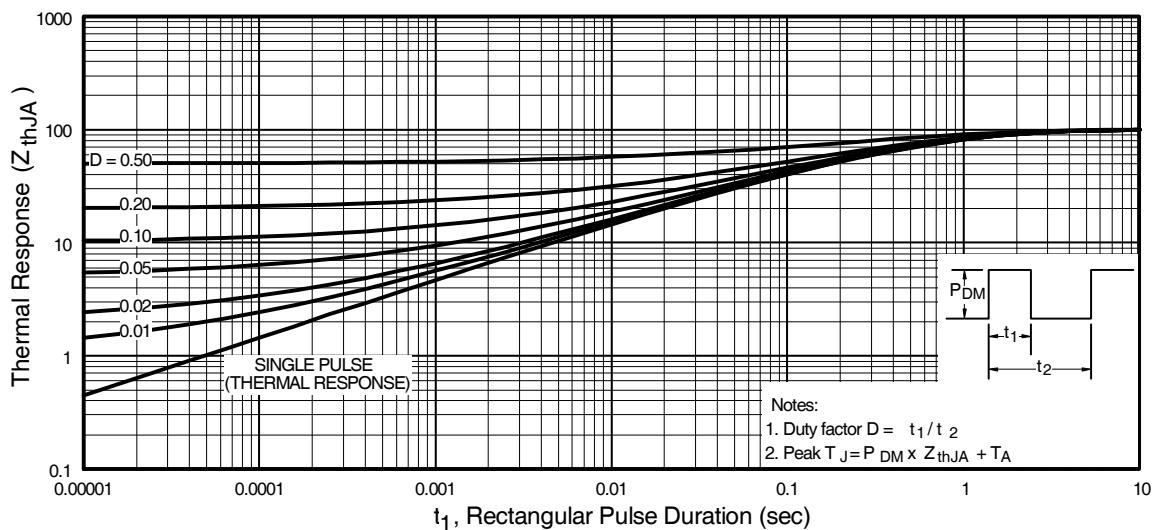
**Fig 8.** Maximum Safe Operating Area



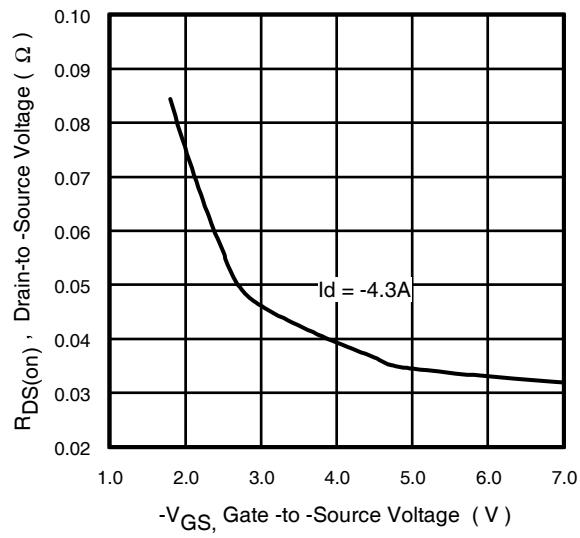
**Fig 9.** Maximum Drain Current Vs.  
Case Temperature



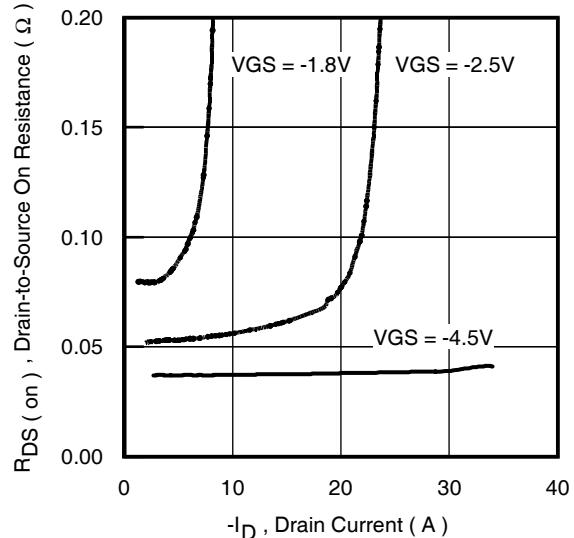
**Fig 10.** Maximum Avalanche Energy  
Vs. Drain Current



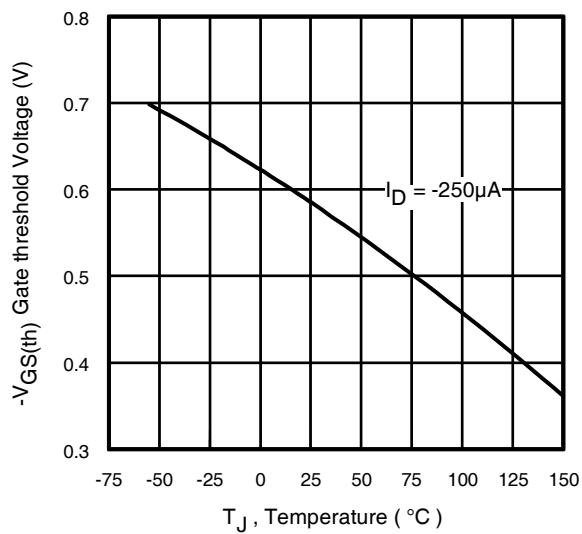
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



**Fig 12.** Typical On-Resistance Vs.  
Gate Voltage



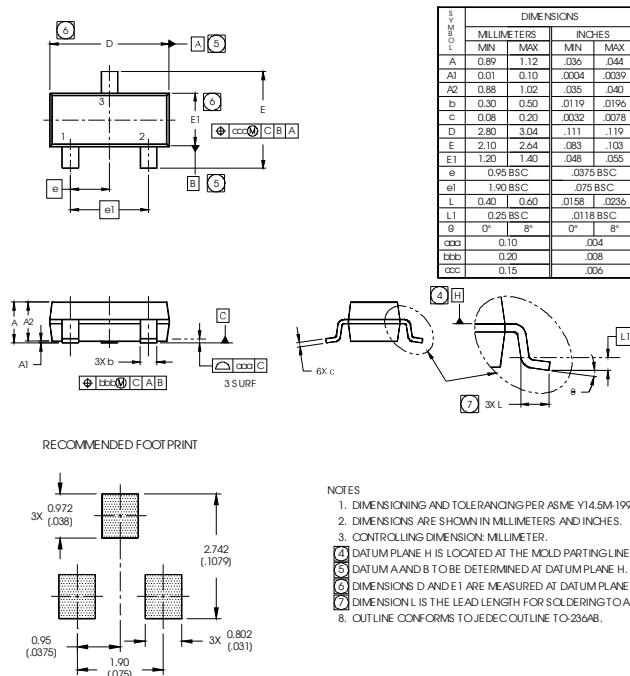
**Fig 13.** Typical On-Resistance Vs.  
Drain Current



**Fig 14.** Typical Threshold Voltage Vs.  
Junction Temperature

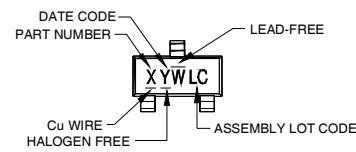
## Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



## Micro3 (SOT-23 / TO-236AB) Part Marking Information

Notes: This part marking information applies to devices produced after 02/26/2001



X = PART NUMBER CODE REFERENCE:

A = IRLML2402	S = IRLML6244
B = IRLML2803	T = IRLML6246
C = IRLML6302	U = IRLML6344
D = IRLML5103	V = IRLML6346
E = IRLML6402	W = IRLML8244
F = IRLML6401	X = IRLML2244
G = IRLML2502	Y = IRLML2246
H = IRLML5203	Z = IRLML9244
I = IRLML0030	
J = IRLML2030	
K = IRLML0100	
L = IRLML0060	
M = IRLML0040	
N = IRLML2060	
P = IRLML9301	
R = IRLML9303	

DATE CODE EXAMPLE:

YWW = 432 = DF  
YWW = 503 = SC

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2011	2001	1	A
2012	2002	2	B
2013	2003	3	C
2014	2004	4	D
2015	2005	5	
2016	2006	6	
2017	2007	7	
2018	2008	8	
2019	2009	9	
2020	2010	0	
		24	X
		25	Y
		26	Z

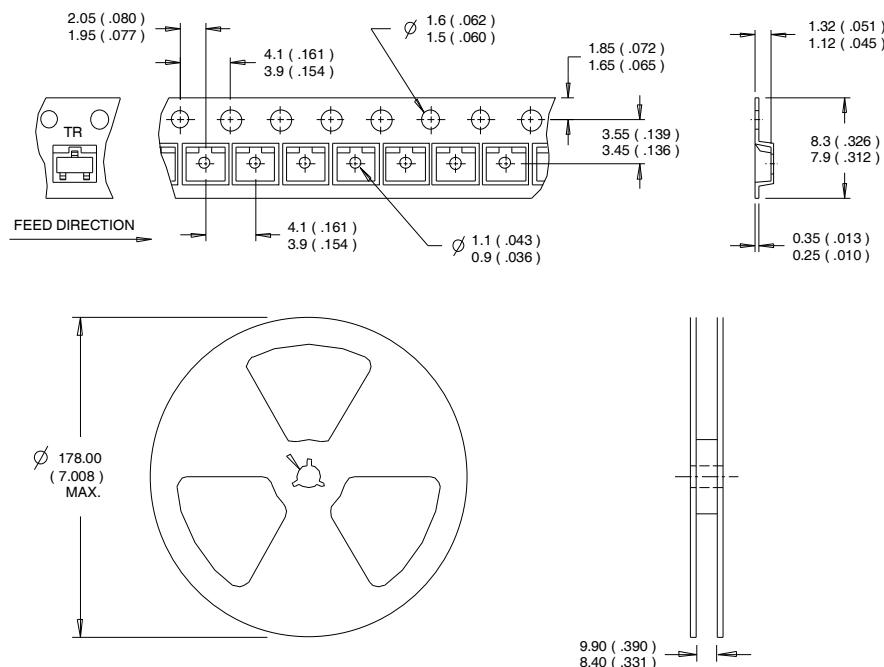
W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2011	2001	A	27
2012	2002	B	28
2013	2003	C	29
2014	2004	D	30
2015	2005	E	
2016	2006	F	
2017	2007	G	
2018	2008	H	
2019	2009	J	
2020	2010	K	
		50	X
		51	Y
		52	Z

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

## Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:  
1. CONTROLLING DIMENSION : MILLIMETER.  
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

**Qualification information<sup>†</sup>**

Qualification level	Consumer (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	Micro3™ (SOT-23)	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

<sup>††</sup> Applicable version of JEDEC standard at the time of product release

**Revision History**

Date	Comment
4/28/2014	<ul style="list-style-type: none"><li>• Updated data sheet with new IR corporate template.</li><li>• Updated package outline &amp; part marking on page 7.</li><li>• Added Qualification table -Qual level "Consumer" on page 9.</li><li>• Added bullet point in the Benefits "RoHS Compliant, Halogen -Free" on page 1.</li></ul>

International  
 Rectifier

**IR WORLD HEADQUARTERS:** 101 N. Sepulveda Blvd., El Segundo, California 90245, USA  
To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>